

### **isc Silicon NPN Power Transistor**

2SC5404

### **DESCRIPTION**

- · High Breakdown Voltage-
  - : V<sub>CBO</sub>= 1500V (Min)
- · High Switching Speed
- Low Saturation Voltage
- · Built-in Damper Diode
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

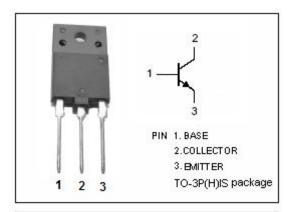
### **APPLICATIONS**

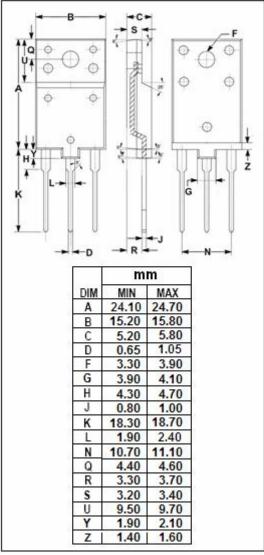
 Horizontal output applications for medium resolution display & color TV.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage 15		V	
V <sub>CEO</sub>	Collector-Emitter Voltage 600		V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current- Continuous 9		Α	
Ісм	Collector Current- Continuous	18	Α	
I <sub>B</sub>	Base Current- Continuous	4.5	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	ion 50		
TJ	Junction Temperature	on Temperature 150		
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	

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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.25A			3.0	٧			
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.25A			1.5	٧			
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			1.0	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	uA			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	10		40				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V	4		8				
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		2.5		MHz			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =1.0MHz		115		pF			
Switching Times									
t <sub>stg</sub>	Storage Time	I <sub>CP</sub> = 5.5A; I <sub>B1</sub> = 1.1A			3.5	μ <b>S</b>			
t <sub>f</sub>	Fall Time	R <sub>L</sub> = 64K Ω			0.3	μ <b>s</b>			

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